Complementary Silicon Plastic Power Transistors

TO-220, NPN & PNP Devices

Complementary silicon plastic power transistors are designed for use as high-frequency drivers in audio amplifiers.

Features

- High Current Gain Bandwidth Product
- TO-220 Compact Package
- Epoxy meets UL 94 V-0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant*

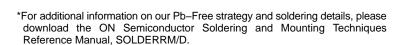
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	350	Vdc
Collector-Base Voltage	V _{CB}	350	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current – Continuous	I _C	4.0	Adc
Collector Current – Peak	I _{CM}	8.0	Adc
Base Current	Ι _Β	1.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	50 0.40	W W/°C
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	2.0 0.016	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C
ESD – Human Body Model	HBM	3B	V
ESD – Machine Model	MM	С	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W



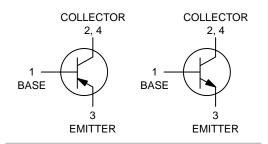


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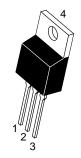
http://onsemi.com

4.0 AMPERES POWER TRANSISTORS COMPLEMENTARY SILICON 350 VOLTS, 50 WATTS

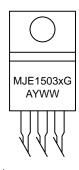
COMPLEMENTARY



MARKING DIAGRAM



TO-220 CASE 221A STYLE 1



MJE1503x = Device Code

x = 4 or 5

A = Location Code

= Year

WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
MJE15034G	TO-220 (Pb-Free)	50 Units / Rail
MJE15035G	TO-220 (Pb-Free)	50 Units / Rail

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 1)	$(I_C = 10 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	350	_	Vdc
Collector Cutoff Current	$(V_{CB} = 350 \text{ Vdc}, I_{E} = 0)$	I _{CBO}	-	10	μAdc
Emitter Cutoff Current	$(V_{BE} = 5.0 \text{ Vdc}, I_{C} = 0)$	I _{EBO}	_	10	μAdc
ON CHARACTERISTICS (Note 1)				•	
DC Current Gain	$ \begin{aligned} &(I_C = 0.1 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}) \\ &(I_C = 0.5 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}) \\ &(I_C = 1.0 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}) \\ &(I_C = 2.0 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}) \end{aligned} $	h _{FE}	100 100 50 10	- - - -	_
Collector-Emitter Saturation Voltage	$(I_C = 1.0 \text{ Adc}, I_B = 0.1 \text{ Adc})$	V _{CE(sat)}	-	0.5	Vdc
Base-Emitter On Voltage	$(I_C = 1.0 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc})$	V _{BE(on)}	-	1.0	Vdc
DYNAMIC CHARACTERISTICS			•		•
Current Gain – Bandwidth Product (Note 2) (I _C = 500 mAdc, V _{CE} = 10 Vdc, f _{test} = 1.0 MHz)		f _T	30	_	MHz

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

^{2.} $f_T = |h_{fe}| \cdot f_{test}$.

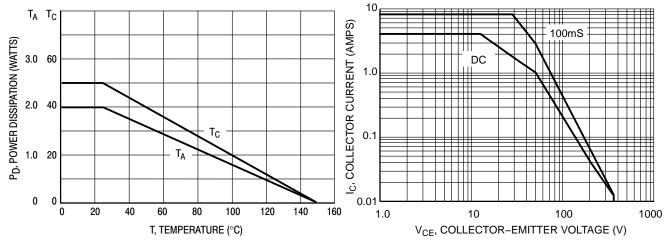


Figure 1. Power Derating

Figure 2. Active Region Safe Operating Area

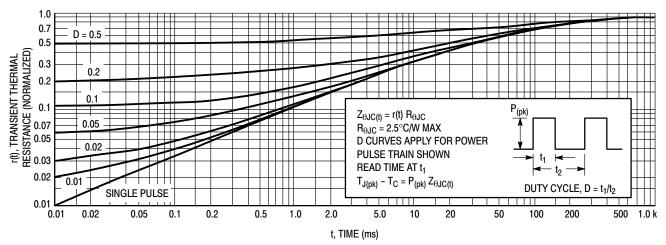


Figure 3. Thermal Response

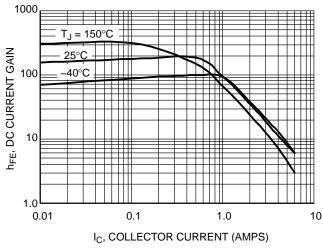


Figure 4. DC Current Gain, V_{CE} = 5.0 V NPN MJE15034

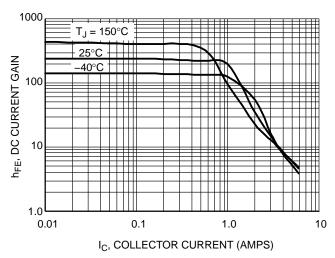


Figure 5. DC Current Gain, V_{CE} = 5.0 V PNP MJE15035

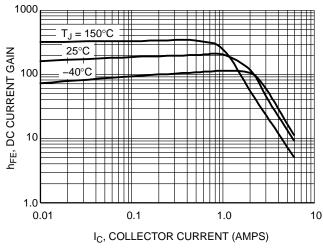


Figure 6. DC Current Gain, V_{CE} = 20 V NPN MJE15034

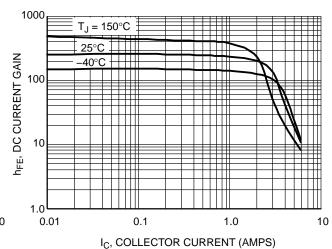


Figure 7. DC Current Gain, V_{CE} = 20 V PNP MJE15035

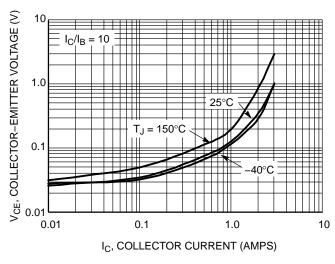
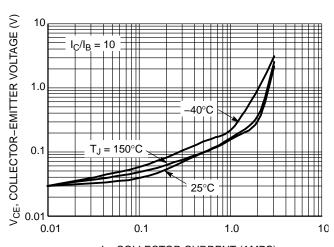


Figure 8. V_{CE(sat)} NPN MJE15034



I_C, COLLECTOR CURRENT (AMPS)

Figure 9. V_{CE(sat)} PNP MJE15035

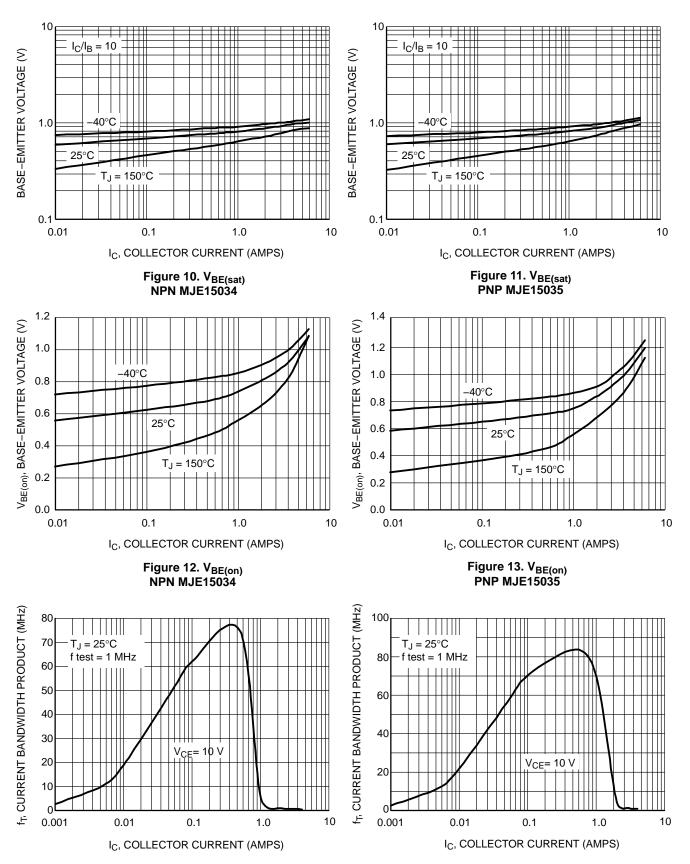
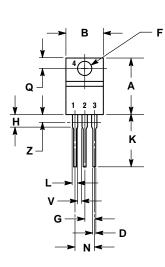


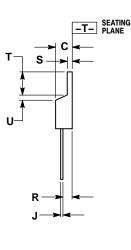
Figure 14. Typical Current Gain Bandwidth Product NPN MJE15034

Figure 15. Typical Current Gain Bandwidth Product PNP MJE15035

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AG**





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14 5M 1982
- T14:3M, 1992: CONTROLLING DIMENSION: INCH. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.036	0.64	0.91	
F	0.142	0.161	3.61	4.09	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.161	2.80	4.10	
J	0.014	0.025	0.36	0.64	
K	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
T	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
٧	0.045		1.15		
Z		0.080		2.04	

PIN 1. BASE

COLLECTOR

EMITTER COLLECTOR

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